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ABSTRACT

0027 A phase change memory structure and method for forming the same, the method including providing a substrate comprising a conductive area; forming a spacer having a partially exposed sidewall region at an upper portion of the spacer defining a phase change memory element contact area; and, wherein the spacer bottom portion partially overlaps the conductive area. Both these two methods can reduce active area of a phase change memory element, therefore, reducing a required phase changing electrical current.